## **MOTORO**LA2供应商 SEMICONDUCTOR TECHNICAL DATA

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by MCR72/D

## **Silicon Controlled Rectifiers Reverse Blocking Triode Thyristors**

... designed for industrial and consumer applications such as temperature, light and speed control; process and remote controls; warning systems; capacitive discharge circuits and MPU interface.

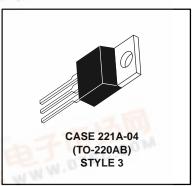
DISC.COM

- Center Gate Geometry for Uniform Current Density
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged Thermowatt Construction for Low Thermal Resistance, High Heat **Dissipation and Durability**
- Low Trigger Currents, 200 μA Maximum for Direct Driving from Integrated Circuits

# **MCR72** Series

SCRs **8 AMPERES RMS** 50 thru 800 VOLTS





MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted.)

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Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage <sup>(1)</sup> $(T_J = -40 \text{ to } 110^{\circ}\text{C}, 1/2 \text{ Sine Wave, } R_{GK} = 1k\Omega)$ MCR72-2 MCR72-3 MCR72-4 MCR72-6 MCR72-8 MCR72-10	VDRM or VRRM	50 100 200 400 600 800	Volts
On-State RMS Current (T <sub>C</sub> = 83°C)	IT(RMS)	8	Amps
Peak Non-repetitive Surge Current (1/2 Cycle, 60 Hz, T <sub>J</sub> = -40 to 110°C)	ITSM	100	Amps
Circuit Fusing (t = 8.3 ms)	l <sup>2</sup> t	40	A <sup>2</sup> s
Peak Gate Voltage (t ≤ 10 μs)	V <sub>GM</sub>	± 5	Volts
Peak Gate Current (t ≤ 10 μs)	IGM	1	Amp
Peak Gate Power (t ≤ 10 μs)	PGM	5	Watts
Average Gate Power	PG(AV)	0.75	Watts
Operating Junction Temperature Range	Тј	-40 to +110	°C

1. VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall hot be tested with a constant current source such that the voltage ratings of the devices are exceeded.

(cont.)

## **MCR72 Series**

#### MAXIMUM RATINGS — continued

Rating	Symbol	Value	Unit
Storage Temperature Range	T <sub>stg</sub>	-40 to + 150	°C
Mounting Torque	—	8	in. lb.
Mounting Torque	—	8	in. lb.

### THERMAL CHARACTERISTICS

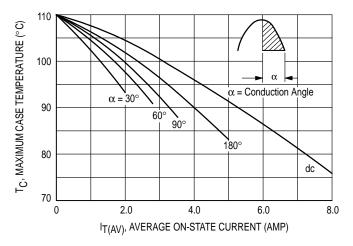
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ extsf{ heta}JC}$	2.2	°C/W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	60	°C/W

**ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C, R<sub>GK</sub> = 1 k $\Omega$  unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Forward or Reverse Blocking Current(1) ( $V_{AK}$ = Rated $V_{DRM}$ or $V_{RRM}$ ) T <sub>J</sub> = 25°C T <sub>J</sub> = 110°C	IDRM <sup>, I</sup> RRM	_		10 500	μΑ μΑ
On-State Voltage (I <sub>TM</sub> = 16 A Peak, Pulse Width ≤ 1 ms, Duty Cycle ≤ 2%)	VTM	_	1.7	2	Volts
Gate Trigger Current (Continuous dc) <sup>(2)</sup> (V <sub>D</sub> = 12 V, R <sub>L</sub> = 100 $\Omega$ )	I <sub>GT</sub>	—	30	200	μA
Gate Trigger Voltage (Continuous dc) $(V_D = 12 V, R_L = 100 \Omega)$ $(V_D = Rated V_{DRM}, R_L = 10 k\Omega, T_J = 110^{\circ}C)$	VGT	 0.1	0.5	1.5 —	Volts
Holding Current (V <sub>D</sub> = 12 V, I <sub>TM</sub> = 100 mA)	lΗ	_		6	mA
Critical Rate-of-Rise of Forward Blocking Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , T <sub>J</sub> = 110°C, Exponential Waveform)	dv/dt	-	10	_	V/µs
Gate Controlled Turn-On Time $(V_D = Rated V_{DRM}, I_{TM} = 16 \text{ A}, I_G = 2 \text{ mA})$	tgt	_	1		μs

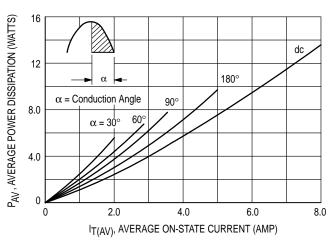
1. Ratings apply for negative gate voltage or R<sub>GK</sub> = 1 kΩ. Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.

2. Does not include  $R_{GK}$  current.



## FIGURE 1 – AVERAGE CURRENT DERATING

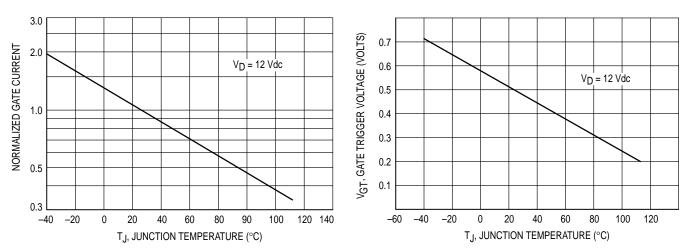
## FIGURE 2 - ON-STATE POWER DISSIPATION



## **MCR72 Series**

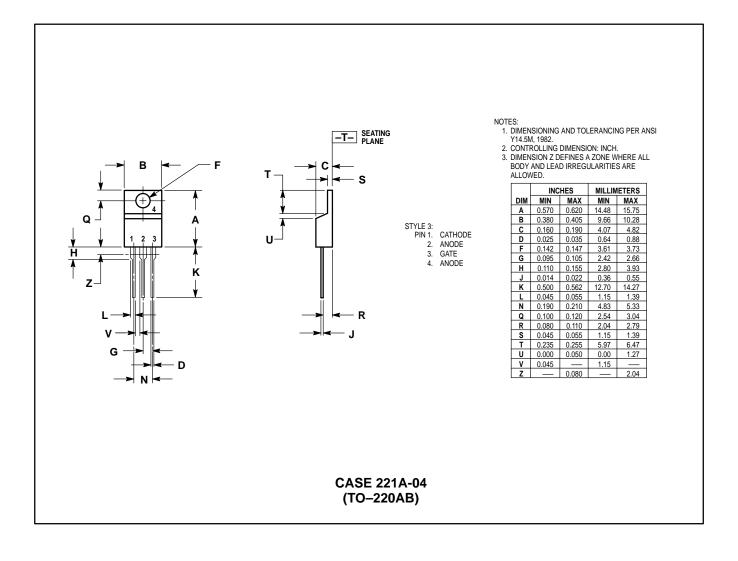
## FIGURE 3 – NORMALIZED GATE CURRENT

FIGURE 4 – GATE VOLTAGE



#### **MCR72 Series**

## PACKAGE DIMENSIONS



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